onsemi

Schottky Barrier Diodes

MBD101G, MMBD101LT1G

Designed primarily for UHF mixer applications but suitable also for use in detector and ultra fast switching circuits. Supplied in an inexpensive plastic package for low cost, high volume consumer requirements. Also available in Surface Mount package.

Features

- Low Noise Figure 6.0 dB Typ @ 1.0 GHz
- Very Low Capacitance Less Than 1.0 pF
- High Forward Conductance 0.5 V (Typ) @ $I_F = 10 \text{ mA}$
- These Devices are Pb Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	7.0	V
Forward Power Dissipation $T_A = 25^{\circ}C$ MBD101 MMBD101LT1 Derate above 25^{C} MBD101 MMBD101LT1	P _F	280 225 2.2 1.8	mW mW/°C
Junction Temperature	TJ	+150	°C
Storage Temperature Range	T _{stg}	_	



= Date Code
= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MBD101G	TO-92 (Pb-Free)	5000 Units / Box
MMBD101LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

		I	0.5	0.6	V
Reverse Leakage $(V_R = 3.0 \text{ V})$	I _R	-	0.02	0.25	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS $(T_A = 25^{\circ}C \text{ unless noted})$

T_A, AMBIENT TEMPERATURE (°C) Figure 1. Reverse Leakage V_F, FORWARD VOLTAGE (VOLTS)

Figure 2. Forward Voltage

V_R, REVERSE VOLTAGE (VOLTS)

Figure 3. Capacitance

PLO, LOCAL OSCILLATOR POWER (mW)

Figure 4. Noise Figure

CASE 182-06



SOT 23 (TO 236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

SOT 23 (TO 236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	
	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE 3.			

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